Docket No. 247561US2/hc

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Takuji MATSUMOTO, et al.

SERIAL NO: 10/754,539 GAU:

FILED: January 12, 2004 EXAMINER:

FOR: SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

■ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

■ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

■ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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STATEMENT OF RELEVANCY

Reference AO (JP 10-209167) on "Form PTO 1449" is discussed in the specification.

Form PTO 1449 (Modified) — U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

ATTY DOCKET NO.	SERIAL NO.
247561US2	10/754,539
APPLICANT: Takuji MATSUMOTO, et al.	
FILING DATE: January 12, 2004	GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
	AO	10-209167	08/07/1998	JAPAN (with English extract)		
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	Y. HIRANO, et al., IEEE International SOI Conference, pages 131-132, "BULK-LAYOUT-COMPATIBLE 0.18μm SOI-CMOS TECHNOLOGY USING BODY-FIXED PARTIAL TRENCH ISOLATION (PTI)", October 1999
	AX	S. MAEDA, et al., Symposium on VLSI Technology Digest of Technical Papers, pages 154-155, "IMPACT OF 0.18μm SOI CMOS TECHNOLOGY USING HYBRID TRENCH ISOLATION WITH HIGH RESISTIVITY SUBSTRATE ON EMBEDDED RF/ANALOG APPLICATIONS", 2000
	AY	Y. HIRANO, et al., IEEE, IEDM, pages 467-470, "IMPACT OF 0.10 μm SOI CMOS WITH BODY-TIED HYBRID TRENCH ISOLATION STRUCTURE TO BREAK THROUGH THE SCALING CRISIS OF SILICON TECHNOLOGY", 2000
	AZ	S. MAEDA, et al., Extended Abstracts of the 2001 International Conference on Solid State Devices and Materials, pages 270-271, "A HIGHLY RELIABLE 0.18 μm SOI CMOS TECHNOLOGY FOR 3.3V/1.8V OPERATION USING HYBRID TRENCH ISOLATION AND DUAL GATE OXIDE", 2001

☐ Additional References sheet(s) attached

Examiner	Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

LIST OF RELATED CASES

Docket Number	Serial or Patent Number	Filing or Issue Date	Inventor/ Applicant
0057-2567-2YY	09/466,934	12/20/99	YAMAGUCHI et al.
221848US2 CONT	10/120,485	04/12/02	YAMAGUCHI et al.
224869US2	10/192,657	07/11/02	MATSUMOTO et al.
226776US2	10/216,363	08/12/02	MATSUMOTO et al.
226976US2	10/237,022	09/09/02	IWAMATSU et al.
247561US2*	10/754,539	01/12/04	MATSUMOTO et al.

*Present Application; listed for information

GJM/akh

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